

DG441/442

Vishay Siliconix

Quad SPST CMOS Analog Switches

DESCRIPTION

The DG441/442 monolithic quad analog switches are designed to provide high speed, low error switching of analog and audio signals. The DG441 has a normally closed function. The DG442 has a normally open function. Combining low on-resistance (50 Ω , typ.) with high speed (t_{ON} 150 ns, typ.), the DG441/442 are ideally suited for upgrading DG201A/202 sockets. Charge injection has been minimized on the drain for use in sample-and-hold circuits.

To achieve high voltage ratings and superior switching performance, the DG441/442 are built on Vishay Siliconix's high-voltage silicon-gate process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks input voltages to the supply levels when off.

FEATURES

- Low On-Resistance: 50 Ω
- Low Leakage: 80 pA
- Low Power Consumption: 0.2 mW
- Fast Switching Action-t_{ON}: 150 ns
- Low Charge Injection-Q: 1 pC
- DG201A/DG202 Upgrades
- TTL/CMOS-Compatible Logic
- Single Supply Capability

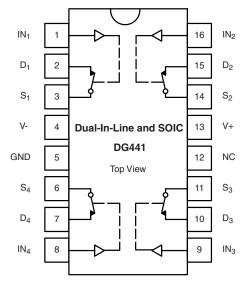
BENEFITS

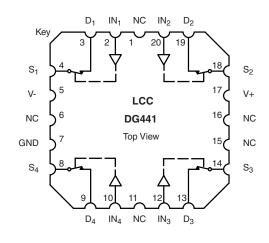
- Less Signal Errors and Distortion
- Reduced Power Supply Requirements
- Faster Throughput
- Improved Reliability
- Reduced Pedestal Errors
- Simplifies Retrofit
- Simple Interfacing

APPLICATIONS

- Audio SwitchingBattery Powered Systems
- Data Acquisition
- Hi-Rel Systems
- Sample-and-Hold Circuits
- Communication Systems
- Automatic Test Equipment
- Medical Instruments

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





TRUTH TABLE

Logic	DG441	DG442
0	ON	OFF
1	OFF	ON

Logic "0" \leq 0.8 V

Logic "1" \ge 2.4 V

* Pb containing terminations are not RoHS compliant, exemptions may apply



RoHS COMPLIANT

Vishay Siliconix



ORDERING INFORM	DRDERING INFORMATION					
Temp Range	Package	Part Number				
	16-Pin Plastic DIP	DG441DJ DG441DJ-E3				
- 40 to 85 °C		DG442DJ DG442DJ-E3				
	16-Pin Narrow SOIC	DG441DY DG441DY-E3 DG441DY-T1 DG441DY-T1-E3				
	IO-FILINATION SOIC	DG442DY DG442DY-E3 DG442DY-T1 DG442DY-T1-E3				

Parameter		Limit	Unit	
V+ to V-		44		
GND to V-		25	V	
Digital Inputs ^a , V _S , V _D		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first		
Continuous Current (Any Terminal)		30	mA	
Current, S or D (Pulsed at 1 ms, 10 % duty cycle)		100	IIIA	
Storage Temperature	(AK Suffix)	- 65 to 150	°C	
	(DJ, DY Suffix)	- 65 to 125		
	16-Pin Plastic DIP ^c	450		
Power Dissipation (Package) ^b	16-Pin CerDIP ^d	900	mW	
	16-Pin Narrow SOIC ^d	900		
	LCC-20 ^d	1200		

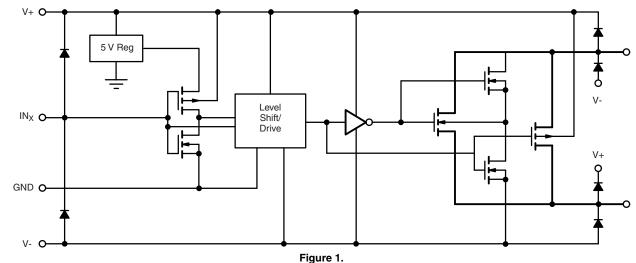
Notes:

a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC Board.

c. Derate 6 mW/°C above 75 °C.

d. Derate 12 mW/°C above 75 °C.

SCHEMATIC DIAGRAM (TYPICAL CHANNEL)





SPECIFICATIONS ^a FOR DUAL SUPPLIES									
		Test Conditions Unless Otherwise Specified V+ = 15 V, V- = - 15 V			-	uffix 125 °C	-	uffix 0 85 °C	
Parameter	Symbol	V _{IN} = 2.4 V, 0.8 V ^f	Temp ^b	Тур ^с	Min ^d	Max ^d	Min ^d	Max ^d	Unit
Analog Switch	•	•				•			
Analog Signal Range ^e	V _{ANALOG}		Full		- 15	15	- 15	15	V
Drain-Source On-Resistance	r _{DS(on)}	I _S = - 10 mA, V _D = ± 8.5 V V+ = 13.5 V, V- = - 13.5 V	Room Full	50		85 100		85 100	Ω
On-Resistance Match Between Channels ^e	$\Delta r_{DS(on)}$	$I_{S} = -10 \text{ mA}, V_{D} = \pm 10 \text{ V}$ V+ = 15 V, V- = -15 V	Room Full			4 5		4 5	52
Switch Off Leakage Current	I _{S(off)}	V+ = 16.5, V- = - 16.5 V	Room Full	± 0.01	- 0.5 - 20	0.5 20	- 0.5 - 5	0.5 5	
Switch On Leakage Suitent	I _{D(off)}	$V_{\rm D} = \pm 15.5 \text{ V}, V_{\rm S} = \pm 15.5 \text{ V}$	Room Full	± 0.01	- 0.5 - 20	0.5 20	- 0.5 - 5	0.5 5	nA
Channel On Leakage Current	I _{D(on)}	V + = 16.5 V, V - = -16.5 V $V_S = V_D = \pm 15.5 V$	Room Full	± 0.08	- 0.5 - 40	0.5 40	- 0.5 - 10	0.5 10	
Digital Control									
Input Current V _{IN} Low	Ι _{ΙL}	V _{IN} under test = 0.8 V, All Other = 2.4 V	Full	- 0.01	- 500	500	- 500	500	nA
Input Current V _{IN} High	I _{IH}	V _{IN} under test = 2.4 V All Other = 0.8 V	Full	0.01	- 500	500	- 500	500	1
Dynamic Characteristics								-	
Turn-On Time	t _{ON}	$R_L = 1 \text{ k}\Omega$, $C_L = 35 \text{ pF}$	Room	150		250		250	
Turn-Off Time DG441	torr	$V_{S} = \pm 10 V$	Room	90		120		120	ns
Charge Injection ^e	Q	See Figure 2 C _L = 1 nF, V _S = 0 V	Room Room	110 - 1		210		210	pC
		$V_{gen} = 0 V, R_{gen} = 0 \Omega$							1
Off Isolation ^e	OIRR	$R_L = 50 \Omega, C_L = 5 pF$	Room	60					dB
Crosstalke (Channel-to-Channel)	X _{TALK}	f = 1 MHz	Room	100					
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz	Room	4					_
Drain Off Capacitance ^e	C _{D(off)}		Room	4					pF
Channel On Capacitance ^e	C _{D(on)}	V _{ANALOG} = 0 V	Room	16					
Power Supplies	1 1	1	F	45		100	1	100	1
Positive Supply Current	l+	V+ = 16.5 V. V- = - 16.5 V	Full Room	15 - 0.0001	- 1	100	- 1	100	-
Negative Supply Current	I-	$V_{\rm IN} = 0 \text{ or } 5 \text{ V}$	Full		- 5		- 5		μA
Ground Current	I _{GND}		Full	- 15	- 100		- 100		

Vishay Siliconix



SPECIFICATIONS ^a FOR SINGLE SUPPLY									
		Test Conditions Unless Otherwise Specified			A Suffix - 55 to 125 °C		D Suffix - 40 to 85 °C		
Parameter	Symbol	V+ = 12 V, V- = 0 V V _{IN} = 2.4 V, 0.8 V ^f	Temp ^b	Тур ^с	Min ^d	Max ^d	Min ^d	Max ^d	Unit
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full		0	12	0	12	V
Drain-Source On-Resistance	r _{DS(on)}	I _S = - 10 mA, V _D = 3 V, 8 V V+ = 10.8 V	Room Full	100		160 200		160 200	Ω
Dynamic Characteristics									
Turn-On Time	t _{ON}	$R_{L} = 1 \text{ k}\Omega, C_{L} = 35 \text{ pF}$	Room	300		450		450	
Turn-Off Time	t _{OFF}	V _S = 8 V See Figure 2	Room	60		200		200	ns
Charge Injection	Q	$C_L = 1nF, V_{gen} = 6 V, R_{gen} = 0 \Omega$	Room	2					рС
Power Supplies									
Positive Supply Current	l+		Full	15		100		100	
Negative Supply Current	I-	V+ = 13.2 V, V- = 0 V V _{IN} = 0 or 5 V	Room Full	- 0.0001	- 1 - 100		- 1 - 100		μA
Ground Current	I _{GND}		Full	- 15	- 100		- 100		

Notes:

a. Refer to PROCESS OPTION FLOWCHART.

b. Room = 25 °C, Full = as determined by the operating temperature suffix.

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

e. Guaranteed by design, not subject to production test.

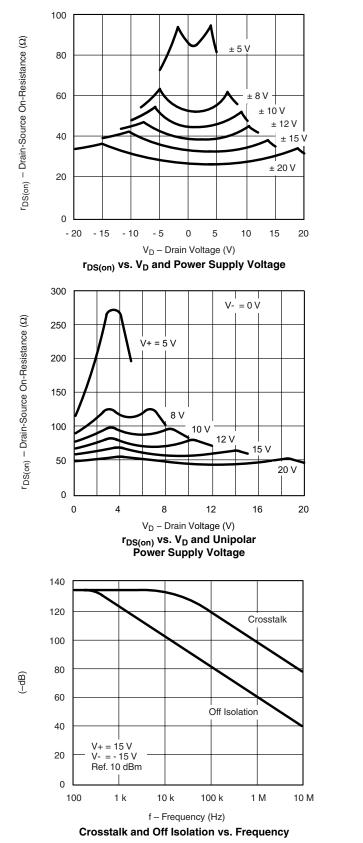
f. V_{IN} = input voltage to perform proper function.

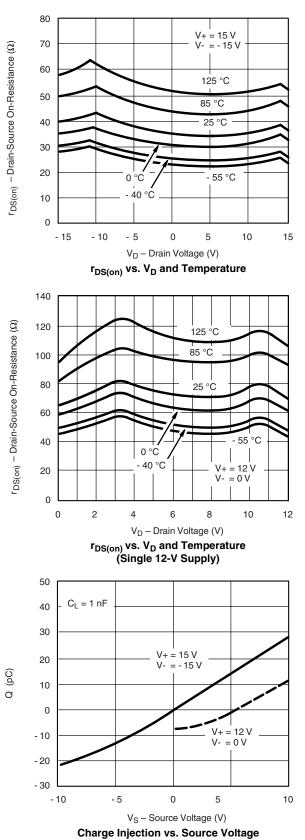
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



DG441/442 Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



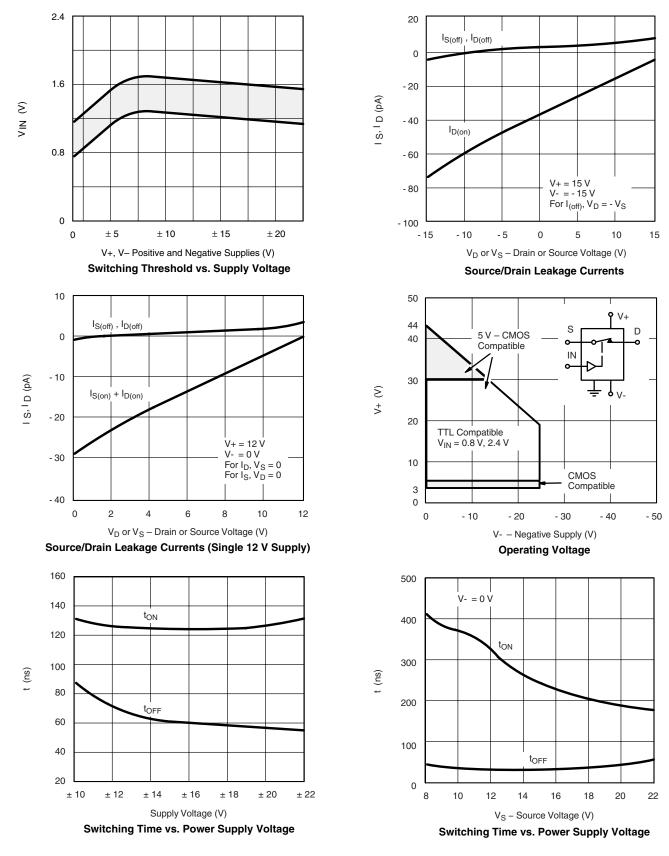


Document Number: 70053 S-71241-Rev. I, 25-Jun-07

DG441/442

Vishay Siliconix









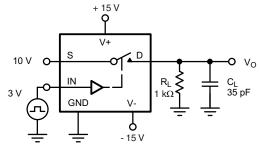
DG441/442 Vishay Siliconix

 ΔV

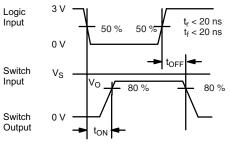
-0

OFF

TEST CIRCUITS



 C_{L} (includes fixture and stray capacitance)

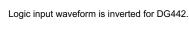


Vo

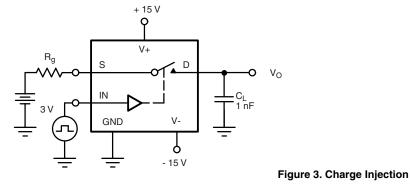
IN_XOFF

(DG441)

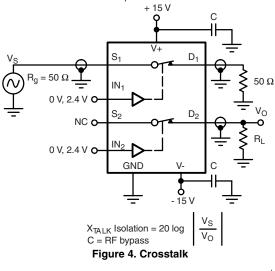
Note: Figure 2. Switching Time

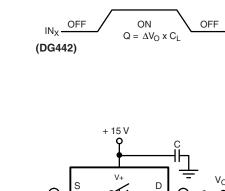


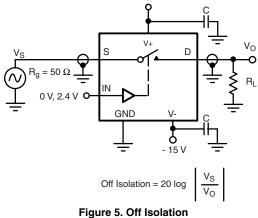
ON



C = 1 mF tantalum in parallel with 0.01 mF ceramic







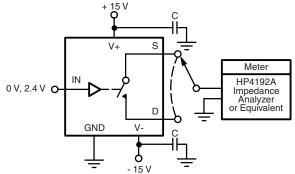


Figure 6. Source/Drain Capacitances

DG441/442

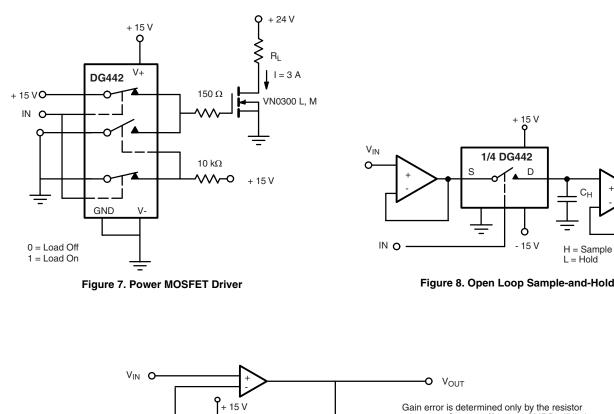
Vishay Siliconix



 V_{OUT}

o

APPLICATIONS



V+

DG441 or DG442

Vδ - 15 V GND

GAIN₁

 $A_V = 1$

GAIN₂

 $A_V = \overline{10}$

 $GAIN_3$ $A_V = 20$

 $\begin{array}{l} \text{GAIN}_4 \\ \text{A}_V = 100 \end{array}$

o

O-

0

0

Gain error is determined only by the resistor tolerance. Op amp offset and CMRR will limit accuracy of circuit.

+ 15 V **o**

D

Q

- 15 V

C_H

H = Sample

L = Hold

With SW₄ Closed

٧

$$\frac{V_{\text{OUT}}}{V_{\text{IN}}} = \frac{R_1 + R_2 + R_3 + R_4}{R_4} = 100$$

Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

R₁ 90 kΩ Ś

R₂ 5 kΩ

R₃ 4 kΩ Ş

R₄ 1 kΩ

Ş

Ş

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?70053.



Vishay

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.